

ABSTRACT OF THE DISCLOSURE

An a-Si film (12) formed on an insulating substrate (10) is irradiated with a laser so that the a-Si film (12) is fused 5 and recrystallized to form a p-Si film (13). Projections (100) generated on the p-Si film (13) at this stage are eliminated by irradiation of ion beams at the incident angle of 60° to 90° using an ion milling method to planarize the surface of the p-Si film (13), thereby creating sufficient 10 insulation between the p-Si film (13) and gate electrodes (15).